## High temperature oxidation behaviour of a hot isostatically pressed silicon nitride-titanium diboride ceramic composite

M. Desmaison-Brut\*, R. Klein\*, A. Feldhoff\*\*, J. Desmaison\*

\*Université de Limoges, Laboratoire de Science des Procédés Céramiques et Traitements de Surface, UMR CNRS 6638,

123, Av. A. Thomas – 87060 Limoges Cedex – France \*\*CECM-CNRS, 15, Rue Georges Urbain 94407 VITRY – France

Hot isostatic pressing has allowed the production of a dense electroconductive silicon nitride-35vol% titanium diboride composite at a temperature which restrains the decomposition of silicon nitride and the reaction between the two powders. Indeed above 1710°C, the formation of silicon, titanium nitride and boron nitride has been observed and proved by X-Ray diffraction analysis.

Nevertheless, a very low amount of additives  $(0.5wt\%Y_2O_3)$  and  $0.25wt\%Al_2O_3$ ) are necessary to achieve good densification without decomposition below 1725°C.

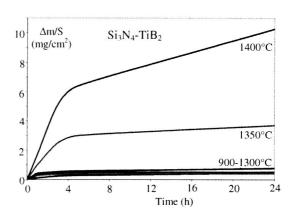
The oxidation mechanism of this dense composite material is analysed.

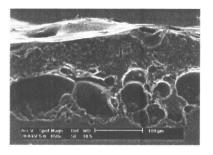
The composite starts to oxidize at about  $700^{\circ}\text{C}$  where titanium diboride  $\text{TiB}_2$  forms rutile and boron sesquioxide  $\text{B}_2\text{O}_3$ . Then, oxidation tests were conducted in flowing oxygen between 900 and 1400°C for 24 hours (Fig. 1). Up to 1300°C, the weight gains are low (less than Img/cm²) and the behaviour may be related to the formation of rutile together with the  $\text{B}_2\text{O}_3$  evaporation.

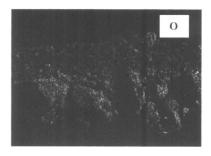
The external oxide scale is thin but a subscale is noticed with titanium depletion.

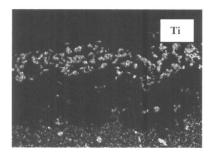
At 1350°C and 1400°C (Fig. 2 and 3), the cristobalite phase is no more observed but there is formation of a fluid borosilicate which embedds the rutile crystals formed during the first hours. The linearity of the kinetics after five hours allows to conclude at a reaction regime. Y-Ti-O-Si needles and platelets on the surface confirms the migration of yttrium through grain boundaries.

This material is more oxidation resistant than a similar hiped silicon nitride -35 vol% titanium nitride composite elaborated without additive.









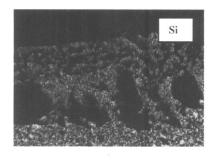


Fig. 1. Isothermal oxidation curves.

Fig. 2. Oxidation at 1400°C, 5 h., O<sub>2</sub>.